SN74CBTLV3257 Low-Voltage 4-Bit 1-of-2 FET Multiplexer/Demultiplexer

1 Features

- 5-Q Switch Connection Between Two Ports
- · Rail-to-Rail Switching on Data I/O Ports
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)

2 Applications

- Internet of Things
- · Wireless Headphones
- Television Set
- 4-Bit Bus Multiplexing and Demultiplexing

3 Description

The SN74CBTLV3257 device is a 4-bit 1-of-2 high-speed FET multiplexer/demultiplexer. The low on-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S) input controls the data flow. The FET multiplexers/demultiplexers are disabled when the output-enable (OE) input is high.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74CBTLV3257DBQ	SSOP (16)	4.90 mm × 3.90 mm
SN74CBTLV3257PW	TSSOP (16)	5.00 mm × 4.40 mm
SN74CBTLV3257DGV	TVSOP (16)	3.60 mm × 4.40 mm
SN74CBTLV3257D	SOIC (16)	9.90 mm × 3.91 mm
SN74CBTLV3257RGY	VQFN (16)	4.00 mm × 3.50 mm
SN74CBTLV3257RSV	UQFN (16)	2.60 mm × 1.80 mm

⁽¹⁾ For all available packages, see the orderable addendum at the end of the datasheet.

Simplified Schematic (Each FET Switch)

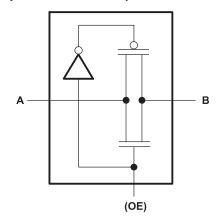
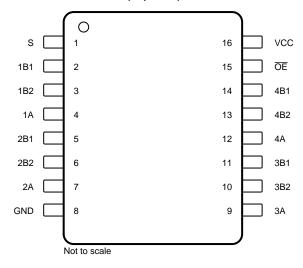


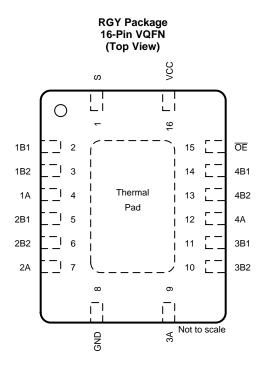
Table of Contents

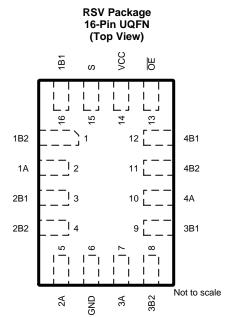
1	Features	1		8.4 Device Functional Modes	8
2	Applications	1	9	Application and Implementation	9
3	Description			9.1 Application Information	
4	Revision History			9.2 Typical Application	9
5	Pin Configuration and Functions		10	Power Supply Recommendations	. 10
6	Specifications		11	Layout	. 11
U	6.1 Absolute Maximum Ratings			11.1 Layout Guidelines	
	6.2 ESD Ratings			11.2 Layout Example	11
	6.3 Recommended Operating Conditions		12	Device and Documentation Support	
	6.4 Thermal Information			12.1 Documentation Support	
	6.5 Electrical Characteristics			12.2 Receiving Notification of Documentation Update	
	6.6 Switching Characteristics			12.3 Community Resources	
7	Parameter Measurement Information			12.4 Trademarks	12
8	Detailed Description			12.5 Electrostatic Discharge Caution	12
0				12.6 Glossary	
			13		
	8.2 Functional Block Diagram			Information	. 12
IOTI	Revision History E: Page numbers for previous revisions may differ ages from Revision L (October 2016) to Revision		ge numb		age
С	hanged the Thermal Information table				5
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Α	dded TSSOP (16) to Device Information table				1
Α	dded Junction temperature, T _J in <i>Absolute Maxim</i>	num Rating	gs		5
С	hanged wording in Detailed Design Procedure to	clarify dev	vice ope	ration	. 10
	-	-	-	Community Resources section	
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A N	emoved Ordering Information table, see Mechani dded Pin Configuration and Functions section, ES dodes, Application and Implementation section, Po	ical, Packa SD Rating ower Supp	s table, oly Reco	nd Orderable Information Feature Description section, Device Functional	1
A N a	emoved Ordering Information table, see Mechanidded Pin Configuration and Functions section, Estados, Application and Implementation section, Pond Documentation Support section, and Mechanic	ical, Packa SD Rating ower Supp cal, Packa	s table, oly Reco aging, an	nd Orderable Information Feature Description section, Device Functional mmendations section, Layout section, Device	1
A N a A	emoved Ordering Information table, see Mechanic dded Pin Configuration and Functions section, ES Modes, Application and Implementation section, Pound Documentation Support section, and Mechanic dded Applications	ical, Packa SD Rating ower Supp cal, Packa	s table, oly Reco	nd Orderable Information	1
A A A	emoved Ordering Information table, see Mechanic dded Pin Configuration and Functions section, ES Modes, Application and Implementation section, Pond Documentation Support section, and Mechanic dded Applications	ical, Packé SD Rating ower Supp cal, Packa	s table, oly Reco	read Orderable Information Feature Description section, Device Functional or mmendations section, Layout section, Device and Orderable Information section	1
A A A	emoved Ordering Information table, see Mechanic dded Pin Configuration and Functions section, ES Modes, Application and Implementation section, Pond Documentation Support section, and Mechanic dded Applications	cal, Packe SD Rating ower Supp cal, Packa	s table, oly Reco aging, an	read Orderable Information Feature Description section, Device Functional or mmendations section, Layout section, Device and Orderable Information section	1 1 1

5 Pin Configuration and Functions

D, DBQ, DGV, and PW Package 16-Pin SOIC, SSOP, TVSOP, and TSSOP (Top View)







Pin Functions

	PIN			
NAME	SOIC, SSOP, TVSOP, TSSOP, VQFN	UQFN	I/O	DESCRIPTION
1A	4	2	I/O	Channel 1 out/in common
1B1	2	16	I/O	Channel 1 in/out 1
1B2	3	1	I/O	Channel 1 in/out 2
2A	7	5	I/O	Channel 2 out/in common
2B1	5	3	I/O	Channel 2 in/out 1
2B2	6	4	I/O	Channel 2 in/out 2
3A	9	7	I/O	Channel 3 out/in common
3B1	11	9	I/O	Channel 3 in/out 1
3B2	10	8	I/O	Channel 3 in/out 2
4A	12	10	I/O	Channel 4 out/in common
4B1	14	12	I/O	Channel 4 in/out 1
4B2	13	11	I/O	Channel 4 in/out 2
GND	8	6	_	Ground
ŌĒ	15	13	1	Output Enable, active low
S	1	15	I	Select
V _{CC}	16	14	_	Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

					MIN	MAX	UNIT
V_{CC}	Supply voltage				-0.5	4.6	V
VI	Input voltage ⁽²⁾			-0.5	4.6	V	
	Continuous channel current					128	mA
I_{IK}	Input clamp current	V _{I/C}) < 0			-50	mA
T_{J}	Junction temperature					150	°C
T _{stg}	Storage temperature				-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	2000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V	V _{IH} High-level control input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
VIH		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
V	V _{IL} Low-level control input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
VIL		V_{CC} = 2.7 V to 3.6 V		0.8	V
T_A	Operating free-air temperature		-40	85	°C

All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See Implications of Slow or Floating CMOS InputsSCBA004.

6.4 Thermal Information

			SN74CBTLV3257					
	THERMAL METRIC ⁽¹⁾	D	DBQ	DGV	PW	RGY	UNIT	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86.7	112.4	123.1	110.9	43.8	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	47.8	63.6	48.7	45.8	57.2	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	43.7	54.8	54.9	56.0	21.4	°C/W	
ψJΤ	Junction-to-top characterization parameter	12.3	17.0	5.2	5.4	1.7	°C/W	
ψJΒ	Junction to baord characterization parameter	43.5	54.4	54.3	55.4	21.5	°C/W	
$R_{\theta JC(botto} \atop m$	Junction-to-case (bottom) thermal resistance	-	-	-	-	9.7	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARA	METER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IK}		$V_{CC} = 3 V$,	I _I = -18 mA				-1.2	V
I _I		$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND				±1	μΑ
I _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 3.6 V				15	μΑ
I _{CC}		$V_{CC} = 3.6 \text{ V},$	$I_{O} = 0$,	$V_I = V_{CC}$ or GND			10	μΑ
$\Delta I_{CC}^{(2)}$	Control	V _{CC} = 3.6 V,	One input at 3 V,	Other inputs at V _{CC} or GND			300	μΑ
Ci	inputs	V _I = 3 V or 0				3		pF
0	A port	V 2 V or 0	$\overline{OE} = V_{CC}$			10.5		l nE
$C_{io(OFF)}$	B port	$V_0 = 3 \text{ V or } 0,$	$V \text{ of } O$, $OE = V_{CC}$			5.5		pF
			V 0	I _I = 64 mA		5	8	
		$V_{CC} = 2.3 \text{ V},$ TYP at $V_{CC} = 2.5 \text{ V}$	$V_1 = 0$	I _I = 24 mA		5	8	
r _{on} (3)		111 at v _{CC} = 2.5 v	V _I = 1.7 V	I _I = 15 mA		27	40	Ω
Ion '		V = 0	I _I = 64 mA		5	7	12	
		$V_{CC} = 3 V$	$v_1 = 3 \text{ V}$	I _I = 24 mA		5	7	
		V _I = 2.4 V	I _I = 15 mA		10	15		

6.6 Switching Characteristics

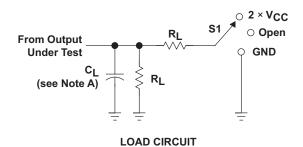
over recommended operating free-air temperature range (unless otherwise noted) (See Figure 1)

PARAMETER	EDOM (INDUIT)	TO (OUTPUT)	$V_{CC} = 2.5 \pm$	0.2 V	V _{CC} = 3.3 V	± 0.3 V	UNIT
PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	MAX	MIN	MAX	UNII
	A or B ⁽¹⁾	B or A		0.15		0.25	20
^T pd	S	A or B	1.8	6.1	1.8	5.3	ns
t _{en}	S	A or B	1.7	6.1	1.7	5.3	ns
t _{dis}	S	A or B	1	4.8	1	4.5	ns
t _{en}	ŌĒ	A or B	1.9	5.6	2	5	ns
t _{dis}	ŌĒ	A or B	1	5.5	1.6	5.5	ns

The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

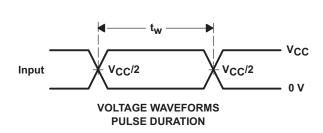
All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
 This is the increase in supply current for each input that is at the specified voltage level, rather than V_{CC} or GND.
 Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

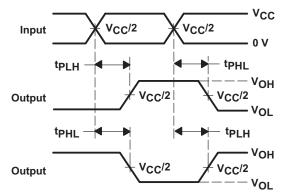
7 Parameter Measurement Information



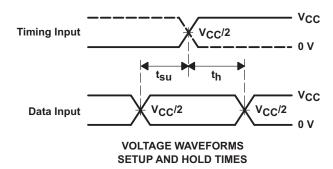
TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	2 × V _{CC}
tPHZ/tPZH	GND

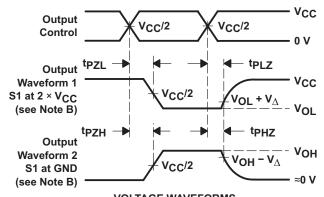
V _{CC}	CL	RL	${f v}_{\!\Delta}$
2.5 V ± 0.2 V	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	50 pF	500 Ω	0.3 V





VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS





VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

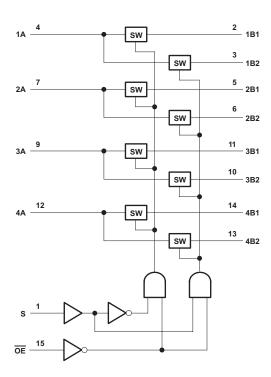
The SN74CBTLV3257 device is a 4-bit 1-of-2 high-speed FET multiplexer and demultiplexer. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S) <u>input</u> controls the data flow. The FET multiplexers and demultiplexers are disabled when the output-enable (OE) input is high.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CBTLV3257 features $5-\Omega$ switch connection between ports, allowing for low signal loss across the switch. Rail-to-rail switching on data I/O allows for full voltage swing outputs. I_{off} supports partial-power-down mode operation, protecting the chip from voltages at output ports when it is not powered on. Latch-up performance exceeds 100 mA per JESD 78, Class II.

8.4 Device Functional Modes

Table 1 shows the functional modes of SN74CBTLV3257.

Table 1. Function Table

INP	UTS	FUNCTION
ŌĒ	S	FUNCTION
L	L	A port = B1 port
L	Н	A port = B2 port
Н	Х	Disconnect

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74CBTLV3257 can be used to multiplex and demultiplex up to 4 channels simultaneously in a 2:1 configuration. The application shown here is a 4-bit bus being multiplexed between two devices. the OE and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.

9.2 Typical Application

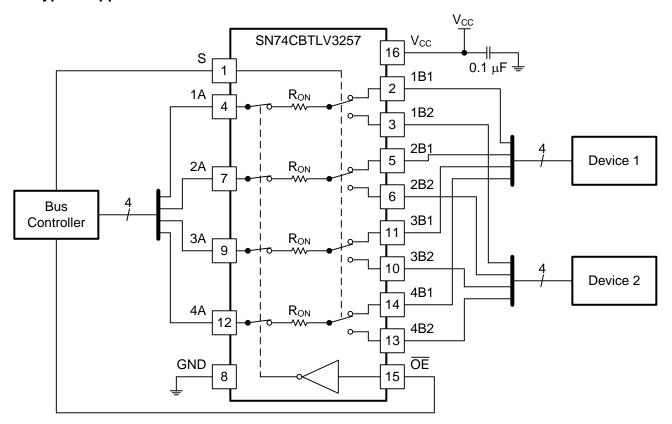


Figure 2. Typical Application of the SN74CBTLV3257

9.2.1 Design Requirements

- Recommended Input Conditions:
 - For specified high and low levels, see V_{IH} and V_{IL} in Recommended Operating Conditions.
 - Inputs and outputs are overvoltage tolerant slowing them to go as high as 4.6 V at any valid V_{CC}.
- 2. Recommended Output Conditions:
 - Load currents should not exceed ±128 mA per channel.
- 3. Frequency Selection Criterion:
 - Maximum frequency tested is 200 MHz.

Typical Application (continued)

 Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in Layout.

9.2.2 Detailed Design Procedure

The 4-bit bus is connected directly to the 1A, 2A, 3A, and 4A ports (known as the xA port) on the SN74CBTLV3257, which essentially splits it into two busses, coming out of the xB1 and xB2 ports. When S is high, xB2 is the active bus, and when S is low, xB1 is the active bus. This means that Device 2 is connected to the bus controller when S is high, and Device 1 is connected to the bus controller when S is low. This setup is especially useful when two devices are hard coded with the same address and only one bus is available. The OE connection can be used to disconnect all devices from the bus controller if necessary.

The 0.1- μ F capacitor on V_{CC} is a decoupling capacitor and should be placed as close as possible to the device.

9.2.3 Application Curve

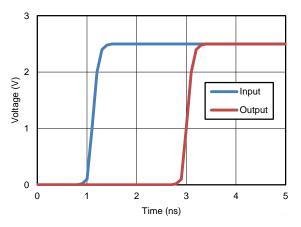


Figure 3. Propagation Delay (t_{pd}) Simulation Result at $V_{CC} = 2.5 \text{ V}$

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 4 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

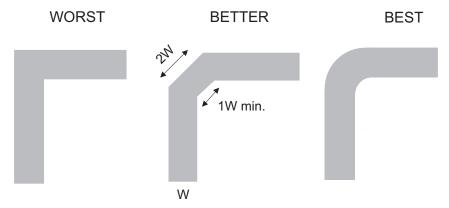


Figure 4. Trace Example

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- Selecting the Right Texas Instruments Signal Switch, SZZA030

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
74CBTLV3257DBQRG4	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
74CBTLV3257DBQRG4.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
74CBTLV3257DBQRG4.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
74CBTLV3257DGVRG4	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
74CBTLV3257DGVRG4.B	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
74CBTLV3257PWRE4	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
74CBTLV3257PWRG4	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
74CBTLV3257PWRG4.B	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
74CBTLV3257RSVRG4	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR
74CBTLV3257RSVRG4.A	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR
74CBTLV3257RSVRG4.B	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR
SN74CBTLV3257D	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	-40 to 85	CBTLV3257
SN74CBTLV3257DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257DBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257DBQR.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257DGVR	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257DGVR.B	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257DR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257
SN74CBTLV3257DR.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257
SN74CBTLV3257DR.B	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257
SN74CBTLV3257PW	Obsolete	Production	TSSOP (PW) 16	-	=	Call TI	Call TI	-40 to 85	CL257
SN74CBTLV3257PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257PWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257PWR.B	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257PWRG4	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257PWRG4.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257PWRG4.B	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257RGYR	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257RGYR.A	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(6)
0N740DTL\(0057D0\(0)D	A - C	Deschartion	\/OFN\/DO\/\\ 40	0000 11 ADOE TOD		. ,		40.1- 05	01.057
SN74CBTLV3257RGYR.B	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257RSVR	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR
SN74CBTLV3257RSVR.A	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR
SN74CBTLV3257RSVR.B	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74CBTLV3257:

Enhanced Product: SN74CBTLV3257-EP

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

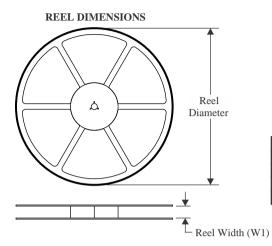
PACKAGE OPTION ADDENDUM

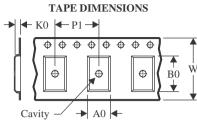
17-Jun-2025

NOTE: Qualified Version Definitions:

● Enhanced Product - Supports Defense, Aerospace and Medical Applications

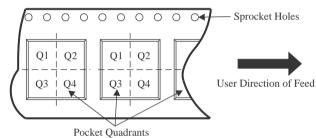
TAPE AND REEL INFORMATION





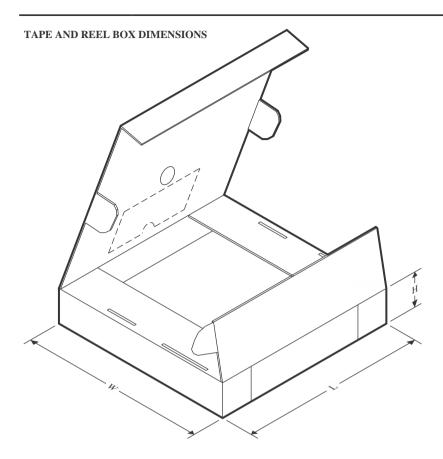
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74CBTLV3257DBQRG4	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
74CBTLV3257DGVRG4	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
74CBTLV3257PWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
74CBTLV3257RSVRG4	UQFN	RSV	16	3000	180.0	13.2	2.1	2.9	0.75	4.0	12.0	Q1
SN74CBTLV3257DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CBTLV3257DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3257DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74CBTLV3257PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257PWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN74CBTLV3257RSVR	UQFN	RSV	16	3000	180.0	13.2	2.1	2.9	0.75	4.0	12.0	Q1

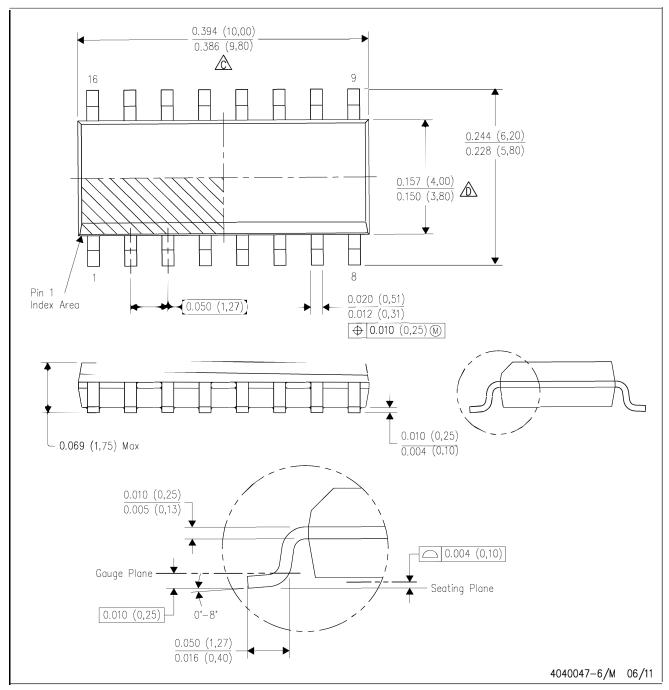


*All dimensions are nominal

All ullilensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74CBTLV3257DBQRG4	SSOP	DBQ	16	2500	353.0	353.0	32.0
74CBTLV3257DGVRG4	TVSOP	DGV	16	2000	367.0	367.0	35.0
74CBTLV3257PWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
74CBTLV3257RSVRG4	UQFN	RSV	16	3000	180.0	180.0	30.0
SN74CBTLV3257DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CBTLV3257DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
SN74CBTLV3257DR	SOIC	D	16	2500	353.0	353.0	32.0
SN74CBTLV3257PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3257PWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3257RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0
SN74CBTLV3257RSVR	UQFN	RSV	16	3000	180.0	180.0	30.0

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE

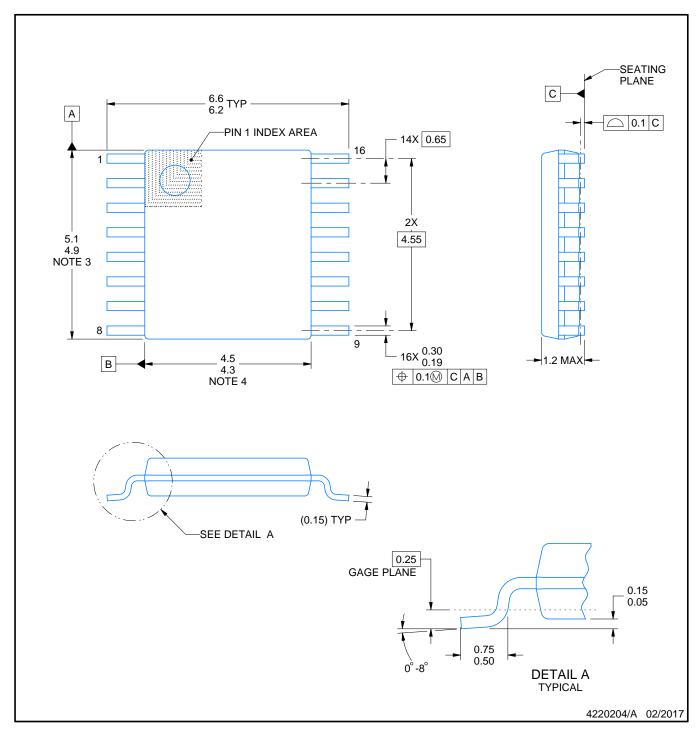


NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



SMALL OUTLINE PACKAGE



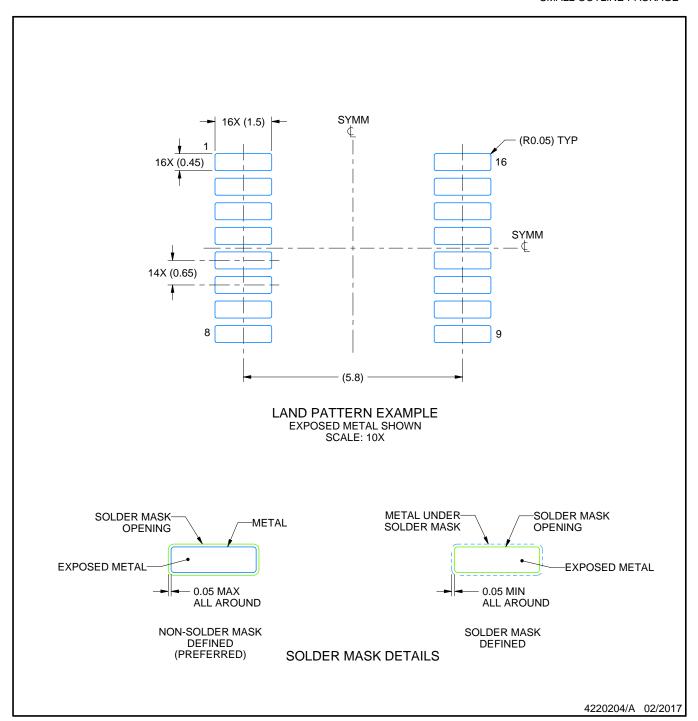
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE PACKAGE



NOTES: (continued)

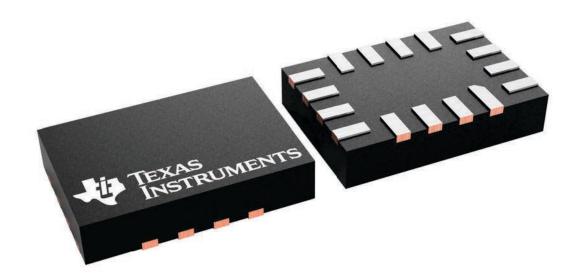
^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{9.} Board assembly site may have different recommendations for stencil design.

1.8 x 2.6, 0.4 mm pitch

ULTRA THIN QUAD FLATPACK - NO LEAD

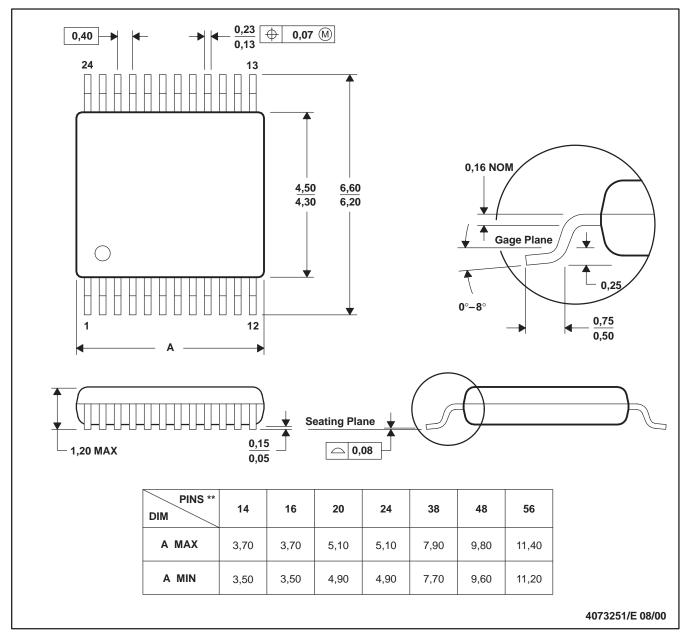
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



DGV (R-PDSO-G**)

24 PINS SHOWN

PLASTIC SMALL-OUTLINE

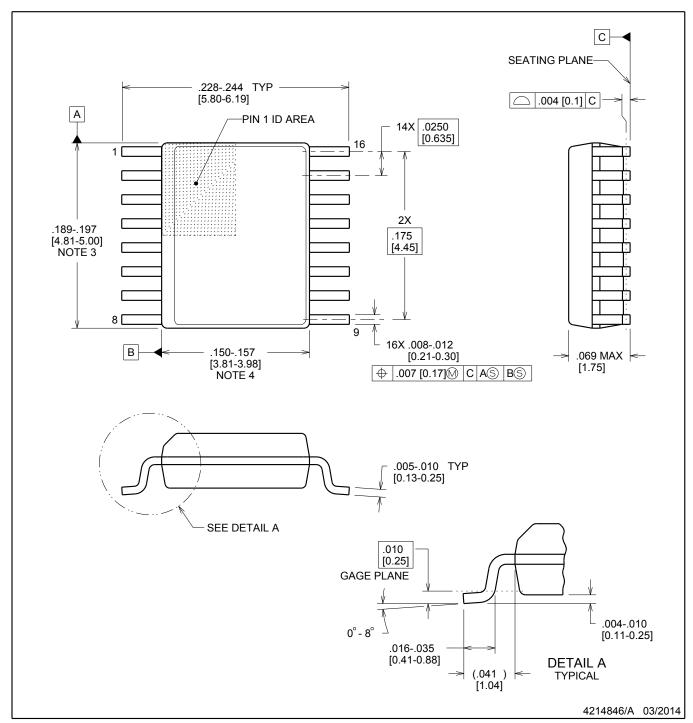


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins MO-153 14/16/20/56 Pins – MO-194



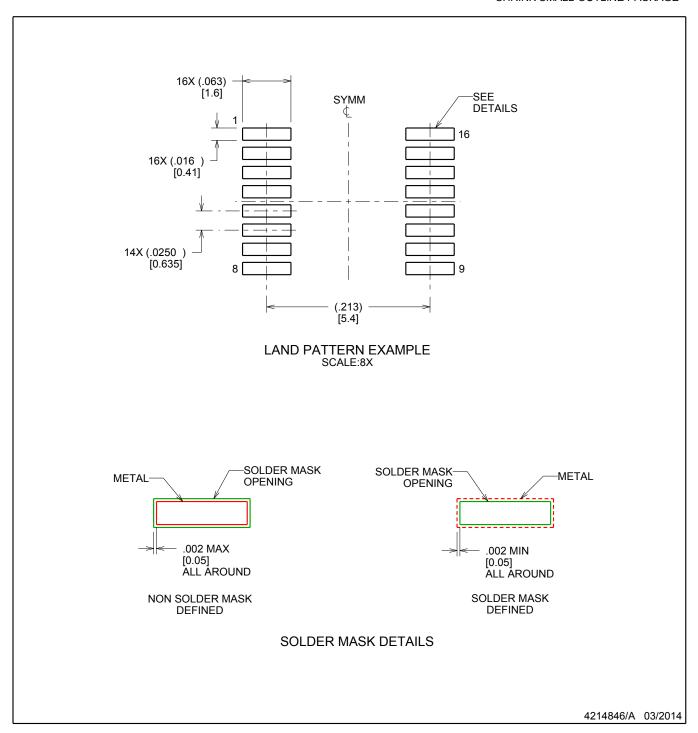
SHRINK SMALL-OUTLINE PACKAGE



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.

SHRINK SMALL-OUTLINE PACKAGE

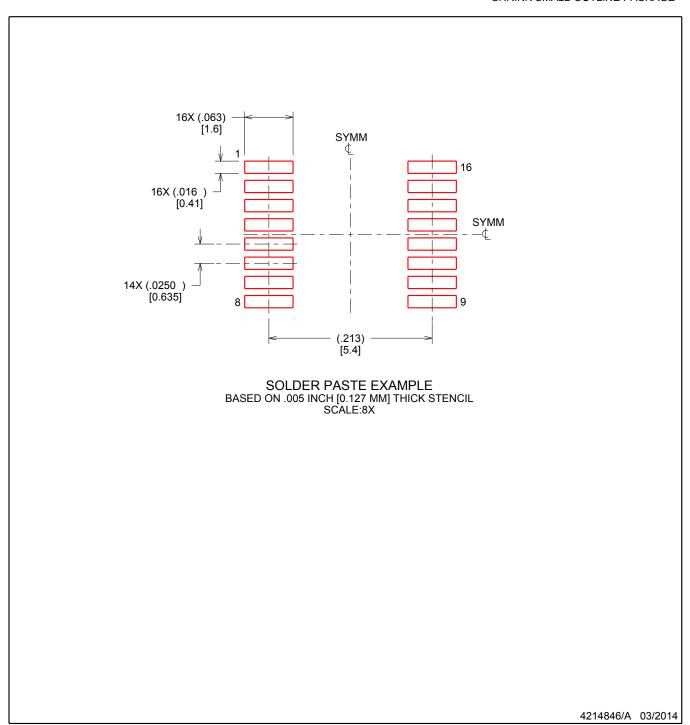


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

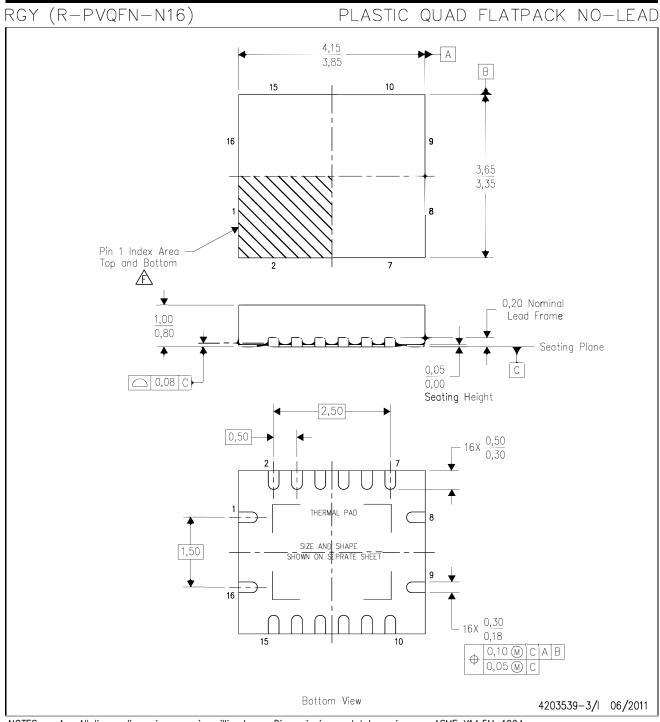
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated.

 The Pin 1 identifiers are either a molded, marked, or metal feature.
 - G. Package complies to JEDEC MO-241 variation BA.

RGY (R-PVQFN-N16)

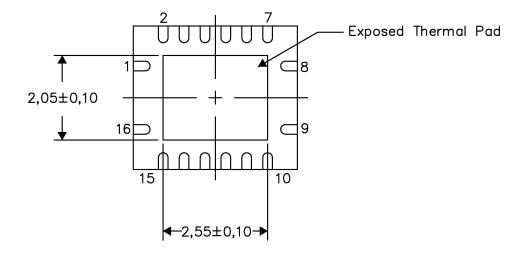
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

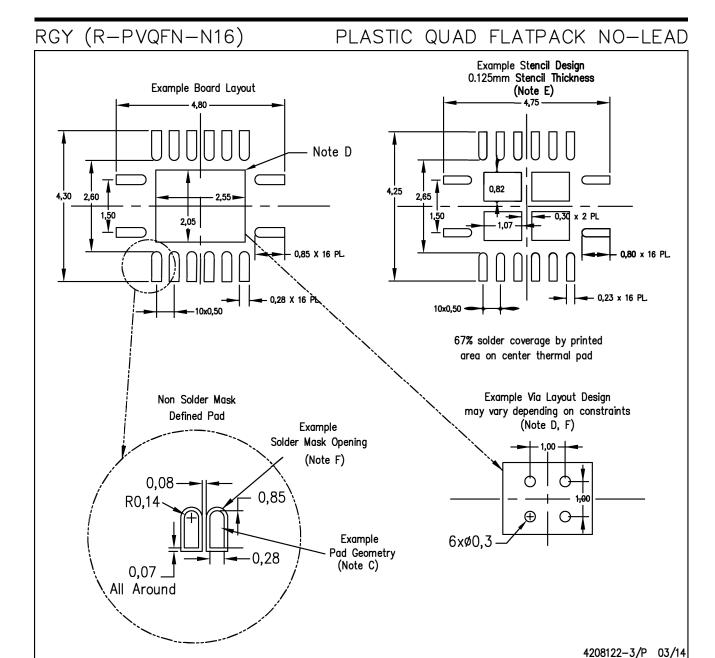


Bottom View

Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.